

**Notice of References Cited**

Application/Control No.

10/595,640

Applicant(s)/Patent Under  
Reexamination  
TSUBATA ET AL.

Examiner

Earl N. Taylor

Art Unit

2818

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.